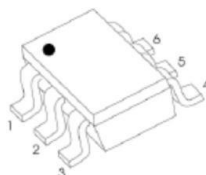


Features

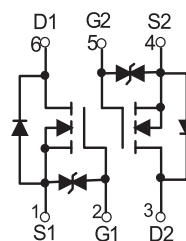
High density cell design for Low $R_{DS(on)}$
Voltage controlled small signal switch
Rugged and reliable
High saturation current capability
ESD protected (2KV HBM)

72K

SOT-363



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	± 20	V
I_D	Drain Current	300	mA
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	$^\circ\text{C} / \text{W}$

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

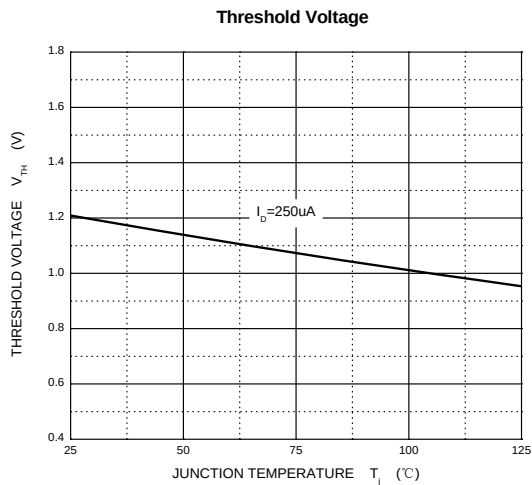
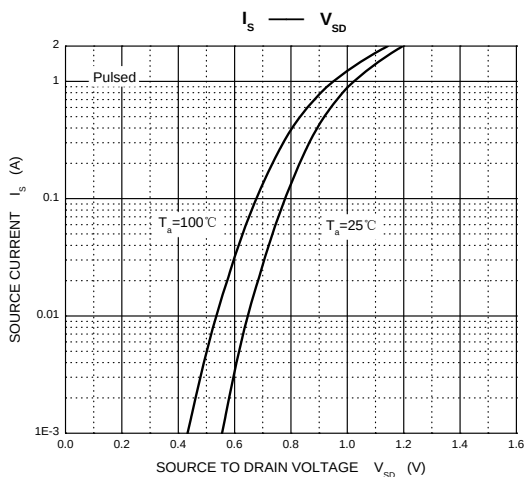
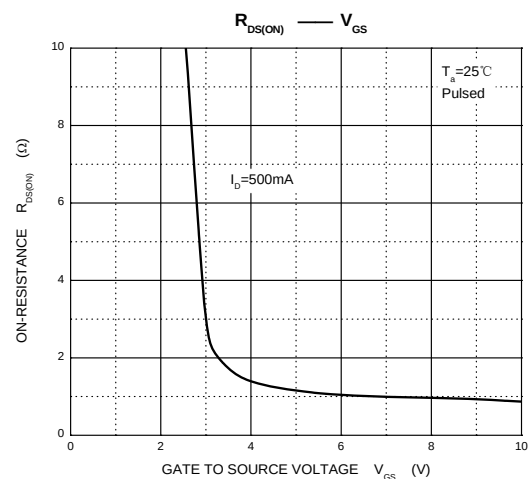
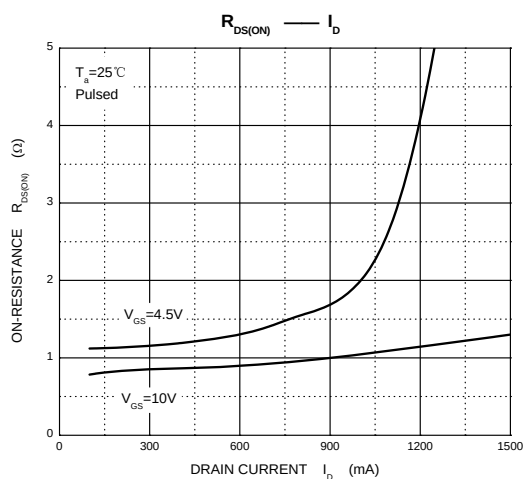
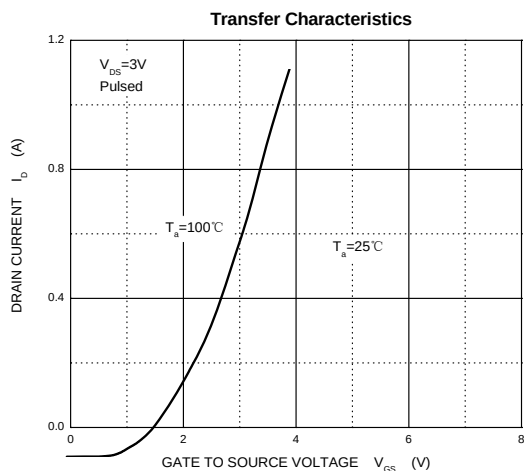
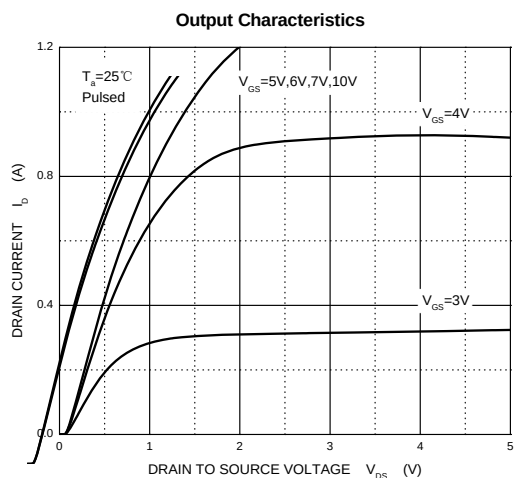
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0V, I _D =250μA	60			V
Gate Threshold Voltage*	V _{GS(th)}	V _{DS} =V _{GS} , I _D =1mA	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} = 0V			1	μA
Gate –Source leakage current	I _{GSS1}	V _{GS} =±20V, V _{DS} = 0V			±10	μA
Drain-Source On-Resistance*	R _{DS(on)}	V _{GS} = 4.5V, I _D =200mA		1.1	5.3	Ω
		V _{GS} =10V, I _D =500mA		0.9	5	Ω
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =300mA			1.5	V
Recovered charge	Q _r	V _{GS} =0V, I _S =300mA, V _R =25V, dI _S /dI _t =-100A/μs		30		nC
Dynamic Characteristics**						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz			40	pF
Output Capacitance	C _{oss}				30	pF
Reverse Transfer Capacitance	C _{rss}				10	pF
Switching Characteristics**						
Turn-On Delay Time	t _{d(on)}	V _{GS} =10V, V _{DD} =50V, R _G =50Ω, R _S =50Ω, R _L =250Ω			10	ns
Turn-Off Delay Time	t _{d(off)}				15	ns
Reverse recovery Time	t _{rr}	V _{GS} =0V, I _S =300mA, V _R =25V, dI _S /dI _t =-100A/μs		30		ns
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV _{GSO}	I _{gs} =±1mA (Open Drain)	±21.5		±30	V

Notes :

*Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

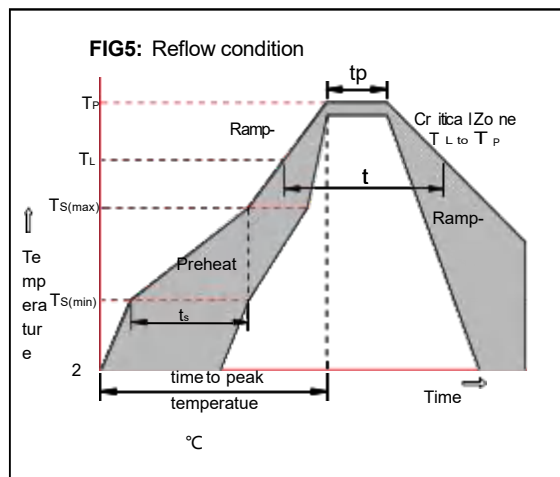
**These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES



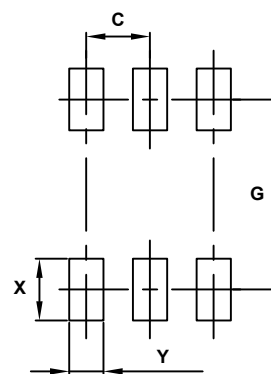
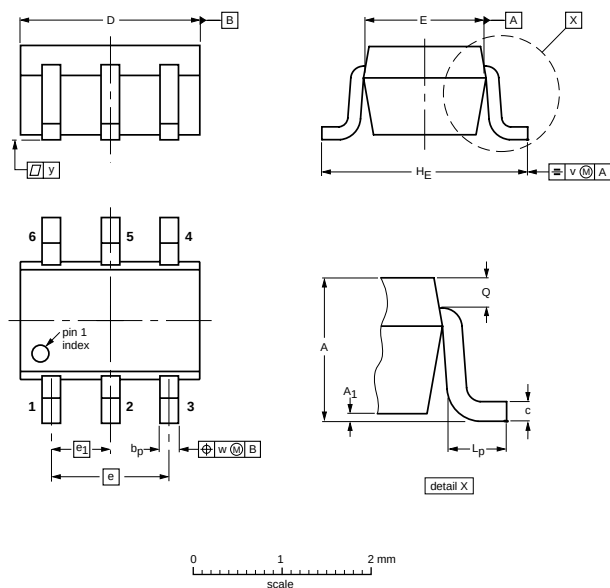
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature (T_L) (Liquid us)	+217 °C
	-Temperature (t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

SOT-363



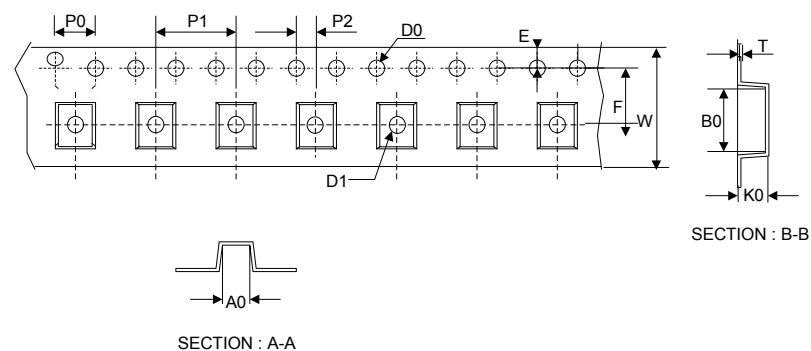
Dimensions	Value (in mm)
C	0.65
G	1.90
X	0.85
Y	0.40

DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

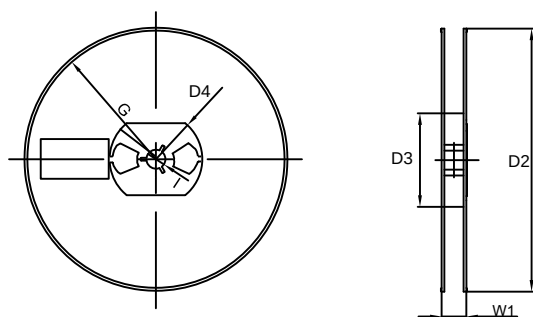
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.00±0.20
E	1.55±0.25
F	3.60±0.20
W	8.00±0.20
A0	3.00±0.20
B0	3.00±0.20
K0	1.30±0.20
T	0.20±0.20
D2	177.0±5.0
D3	55Min.
D4	R24.6±2.0
G	R82.0±2.0
I	13.0±2.0
W1	10.20±3.0

7" Reel



Quantity: 3000PCS